

1 Characteristics

Table 2. Absolute maximum ratings

| Symbol | Parameter | | | Value | Unit |
|--------------------|--|-------------------------------|-------------------------------------|--------------------------------|------------------------|
| $I_{T(RMS)}$ | On-state rms current (full sine wave) | | $T_c = 141\text{ }^{\circ}\text{C}$ | 4 | A |
| I_{TSM} | Non repetitive surge peak on-state current (full cycle, T_j initial = $25\text{ }^{\circ}\text{C}$) | $F = 60\text{ Hz}$ | $t = 16.7\text{ ms}$ | 42 | A |
| | | $F = 50\text{ Hz}$ | $t = 20\text{ ms}$ | 40 | |
| I^2t | I^2t Value for fusing | $t_p = 10\text{ ms}$ | | 11 | A^2s |
| di/dt | Critical rate of rise of on-state current $I_G = 2 \times I_{GT}$, $t_r \leq 100\text{ ns}$ | $F = 120\text{ Hz}$ | $T_j = 150\text{ }^{\circ}\text{C}$ | 50 | $\text{A}/\mu\text{s}$ |
| V_{DSM}/V_{RSM} | Non repetitive surge peak off-state voltage | $t_p = 10\text{ ms}$ | $T_j = 25\text{ }^{\circ}\text{C}$ | $V_{DRM}/V_{RRM} + 100$ | V |
| I_{GM} | Peak gate current | $t_p = 20\text{ }\mu\text{s}$ | $T_j = 150\text{ }^{\circ}\text{C}$ | 4 | A |
| $P_{G(AV)}$ | Average gate power dissipation | | $T_j = 150\text{ }^{\circ}\text{C}$ | 1 | W |
| T_{stg} T_j | Storage junction temperature range Operating junction temperature range | | | - 40 to + 150 - 40 to + 150 | $^{\circ}\text{C}$ |

Table 3. Electrical characteristics ($T_j = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)

| Symbol | Test conditions | Quadrant | Min. | Max. | Unit |
|-------------------|---|--------------|------|------|------------------------|
| I_{GT} | $V_D = 12\text{ V}$ $R_L = 33\text{ }\Omega$ | I - II - III | 1 | 10 | mA |
| V_{GT} | | I - II - III | | 1.0 | V |
| V_{GD} | $V_D = V_{DRM}$, $R_L = 3.3\text{ k}\Omega$ | I - II - III | 0.15 | | V |
| $I_H^{(1)}$ | $I_T = 100\text{ mA}$ | | | 25 | mA |
| I_L | $I_G = 1.2 I_{GT}$ | I - III | | 30 | mA |
| | | II | | 35 | |
| $dV/dt^{(1)}$ | $V_D = 67\% V_{DRM}$, gate open, $T_j = 150\text{ }^{\circ}\text{C}$ | | 75 | | $\text{V}/\mu\text{s}$ |
| $(di/dt)_c^{(1)}$ | Logic level, $0.1\text{ V}/\mu\text{s}$, $T_j = 150\text{ }^{\circ}\text{C}$ | | 5.7 | | A/ms |
| | Logic level, $15\text{ V}/\mu\text{s}$, $T_j = 150\text{ }^{\circ}\text{C}$ | | 1.5 | | |

1. For both polarities of A2 referenced to A1.

Table 4. Static characteristics

| Symbol | Test conditions | | | Value | Unit |
|------------------------|--|---------------------------|------|-------|---------------|
| $V_T^{(1)}$ | $I_{TM} = 5.6 \text{ A}$, $t_p = 380 \mu\text{s}$ | $T_j = 25^\circ\text{C}$ | MAX. | 1.5 | V |
| $V_{T0}^{(1)}$ | Threshold voltage | $T_j = 150^\circ\text{C}$ | MAX. | 0.80 | V |
| $R_d^{(1)}$ | Dynamic resistance | $T_j = 150^\circ\text{C}$ | MAX. | 80.0 | m Ω |
| I_{DRM} I_{RRM} | $V_{DRM} = V_{RRM}$ | $T_j = 25^\circ\text{C}$ | MAX. | 5 | μA |
| | | $T_j = 150^\circ\text{C}$ | MAX. | 2.2 | mA |
| | $V_D/V_R = 400 \text{ V}$ (at peak mains voltage) | $T_j = 150^\circ\text{C}$ | MAX. | 1.75 | |
| | $V_D/V_R = 200 \text{ V}$ (at peak mains voltage) | $T_j = 150^\circ\text{C}$ | MAX. | 1.5 | |

1. for both polarities of A2 referenced to A1.

Table 5. Thermal resistance

| Symbol | Parameter | Value | Unit |
|---------------|-----------------------|-------|--------------------|
| $R_{th(j-c)}$ | Junction to case (AC) | 2.20 | $^\circ\text{C/W}$ |
| $R_{th(j-a)}$ | Junction to ambient | 60 | |

Figure 1. Maximum power dissipation versus on-state rms current (full cycle) **Figure 2. On-state rms current versus case temperature (full cycle)**

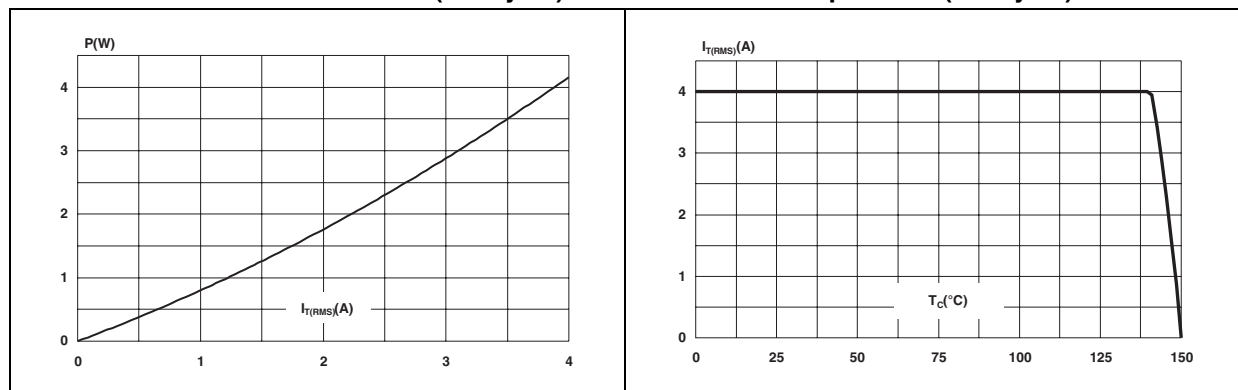


Figure 3. On-state rms current versus ambient temperature (free air convection, full cycle) **Figure 4. Relative variation of thermal impedance, versus pulse duration**

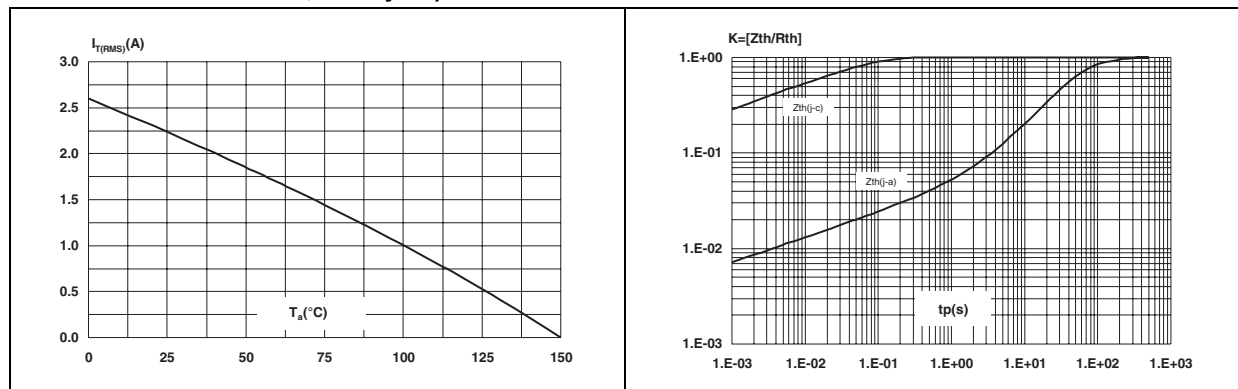


Figure 5. Relative variation of gate trigger current and voltage versus junction temperature (typical values)

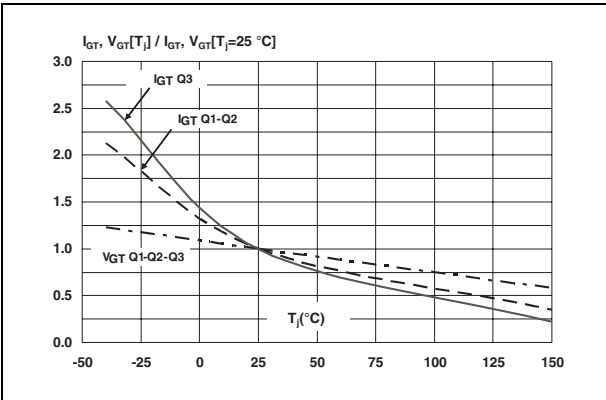


Figure 6. Relative variation of holding and latching current versus junction temperature (typical values)

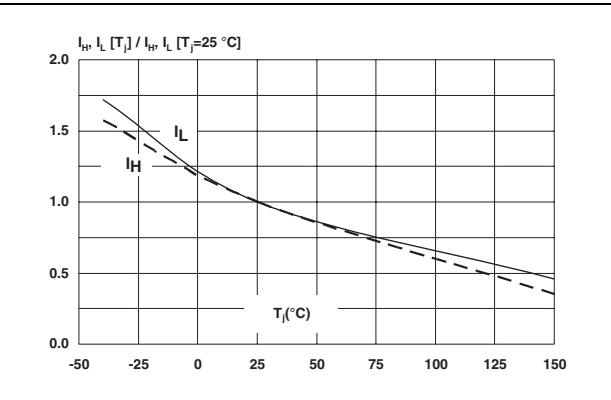


Figure 7. Surge peak on-state current versus number of cycles

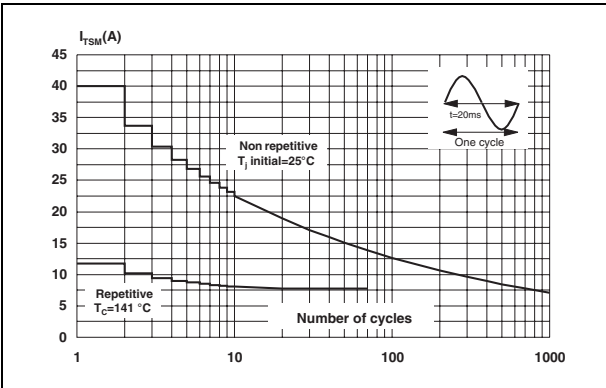


Figure 8. Non-repetitive surge peak on-state current and corresponding value of I²t

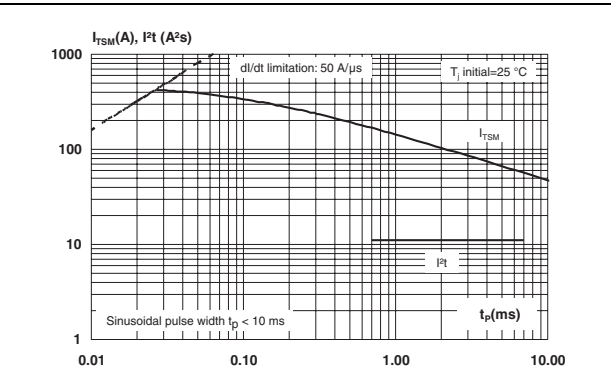


Figure 9. On-state characteristics (maximum values)

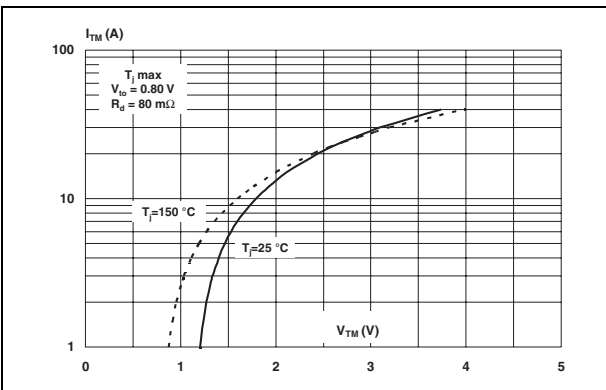


Figure 10. Relative variation of critical rate of decrease of main current versus junction temperature

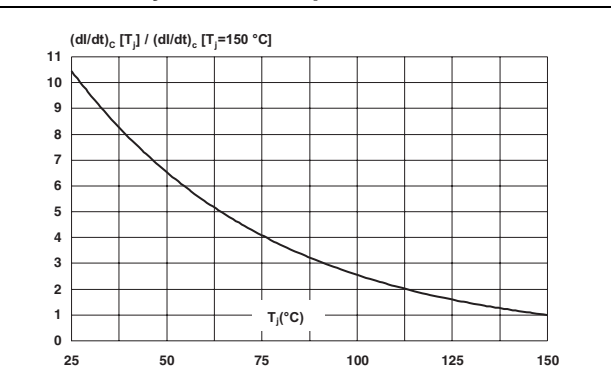


Figure 11. Relative variation of critical rate of decrease of main current versus reapplied dV/dt (typical values)

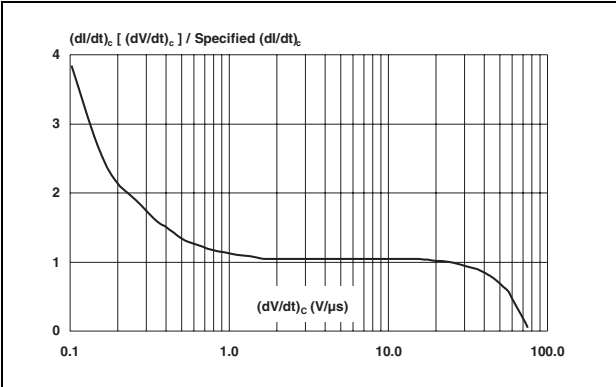


Figure 12. Relative variation of static dV/dt immunity versus junction temperature

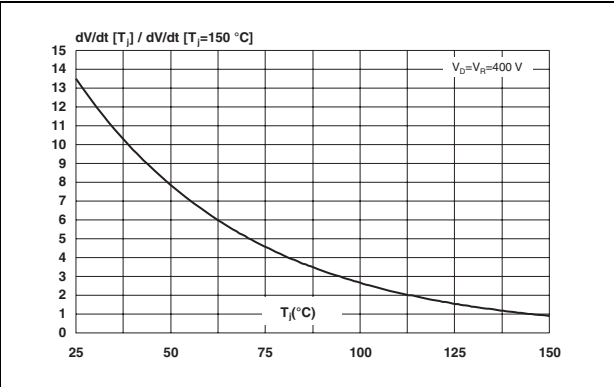


Figure 13. Variation of leakage current versus junction temperature for different values of blocking voltage

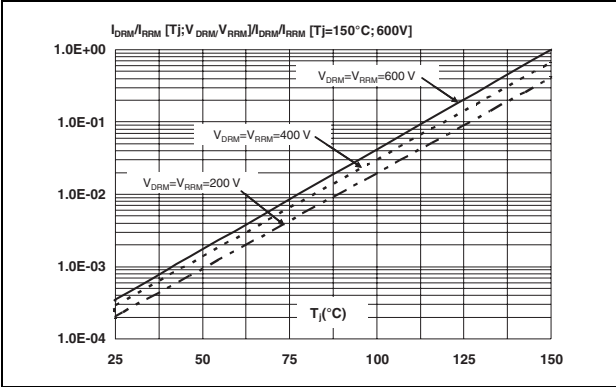
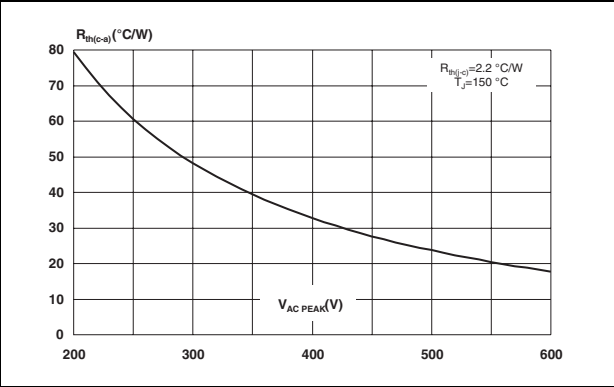
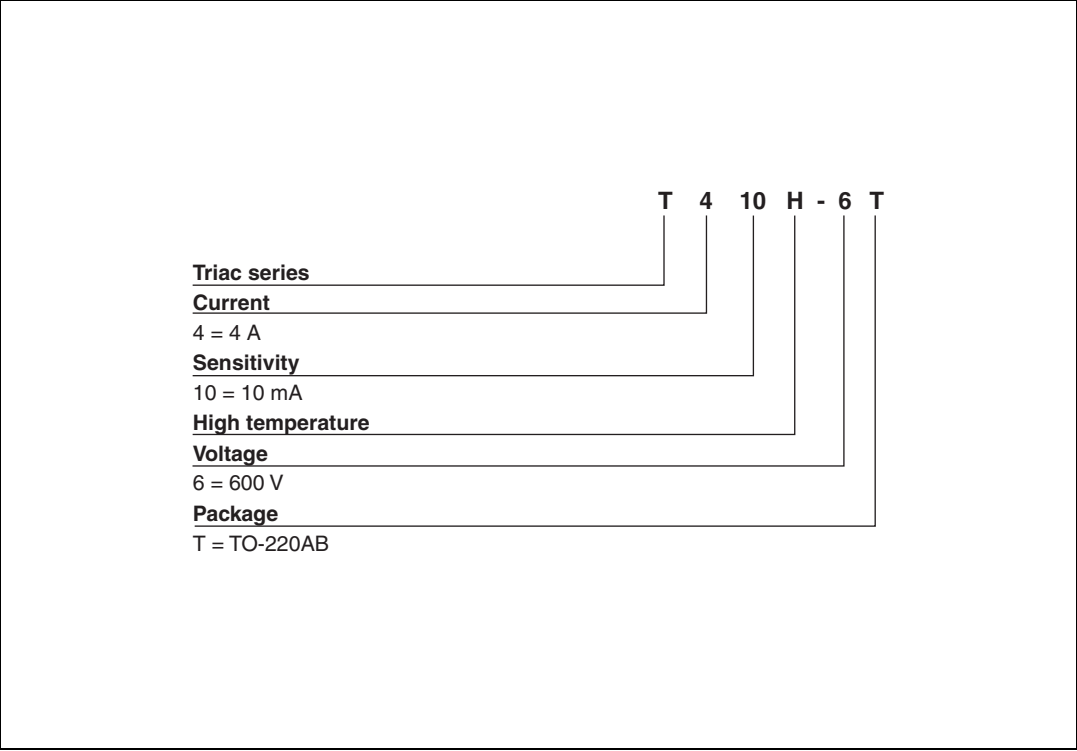


Figure 14. Acceptable case to ambient thermal resistance versus repetitive peak off-state voltage



2 Ordering information scheme

Figure 15. Ordering information scheme



3 Package information

- Epoxy meets UL94, V0
- Recommended torque 0.4 to 0.6 N·m

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Table 6. TO-220AB dimensions

| Ref. | Dimensions | | | | | |
|------|-------------|-------|-------|--------|-------|-------|
| | Millimeters | | | Inches | | |
| | Min. | Typ. | Max. | Min. | Typ. | Max. |
| A | 15.20 | | 15.90 | 0.598 | | 0.625 |
| a1 | | 3.75 | | | 0.147 | |
| a2 | 13.00 | | 14.00 | 0.511 | | 0.551 |
| B | 10.00 | | 10.40 | 0.393 | | 0.409 |
| b1 | 0.61 | | 0.88 | 0.024 | | 0.034 |
| b2 | 1.23 | | 1.32 | 0.048 | | 0.051 |
| C | 4.40 | | 4.60 | 0.173 | | 0.181 |
| c1 | 0.49 | | 0.70 | 0.019 | | 0.027 |
| c2 | 2.40 | | 2.72 | 0.094 | | 0.107 |
| e | 2.40 | | 2.70 | 0.094 | | 0.106 |
| F | 6.20 | | 6.60 | 0.244 | | 0.259 |
| ØI | 3.75 | | 3.85 | 0.147 | | 0.151 |
| I4 | 15.80 | 16.40 | 16.80 | 0.622 | 0.646 | 0.661 |
| L | 2.65 | | 2.95 | 0.104 | | 0.116 |
| I2 | 1.14 | | 1.70 | 0.044 | | 0.066 |
| I3 | 1.14 | | 1.70 | 0.044 | | 0.066 |
| M | | 2.60 | | | 0.102 | |

4 Ordering information

Table 7. Ordering information

| Order code | Marking | Package | Weight | Base qty | Delivery mode |
|------------|----------|----------|--------|----------|---------------|
| T410H-6T | T410H 6T | TO-220AB | 2.3 g | 50 | Tube |

5 Revision history

Table 8. Document revision history

| Date | Revision | Changes |
|-------------|----------|--------------|
| 15-May-2009 | 1 | First issue. |

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